# **BGU6102**

# Wideband silicon low-noise amplifier MMIC Rev. 3 — 13 July 2012

**Product data sheet** 

#### **Product profile** 1.

#### 1.1 General description

The BGU6102 MMIC is an unmatched wideband MMIC featuring an integrated bias, enable function and wide supply voltage. BGU6102 is part of a family of three products (BGU6101, BGU6102 and BGU6104) and is optimized for 2 mA operation.

#### 1.2 Features and benefits

- Supply voltage range from 1.5 V to 5 V
- Current range up to 20 mA at 3 V and 40 mA at 5 V supply voltage
- NF<sub>min</sub> of 0.7 dB
- Applicable between 40 MHz and 4 GHz
- Integrated temperature-stabilized bias for easy design
- Bias current configurable with external resistor
- Power-down mode current consumption < 6 μA</p>
- ESD protection on all pins up to 3 kV HBM
- Small 6-pin leadless package 2.0 mm × 1.3 mm × 0.35 mm

#### 1.3 Applications

- FM radio
- Mobile TV, CMMB
- ISM
- Wireless security

- RKE, TPMS
- AMR, ZigBee, Bluetooth
- WiFi, WLAN (2.4 GHz)
- Low current applications

#### 1.4 Quick reference data

#### Quick reference data

| Symbol       | Parameter            | Conditions                                | Min | Тур  | Max | Unit |
|--------------|----------------------|---|-----|------|-----|------|
| $ s_{21} ^2$ | insertion power gain | f = 450 MHz                               | -   | 18.5 | -   | dB   |
|              |                      | f = 900 MHz                               | -   | 16.5 | -   | dB   |
|              |                      | f = 2400 MHz; I <sub>CC(tot)</sub> = 6 mA | -   | 14.0 | -   | dB   |
| $NF_{min}$   | minimum noise figure | f = 450 MHz                               | -   | 0.7  | -   | dB   |
|              |                      | f = 900 MHz                               | -   | 8.0  | -   | dB   |
|              |                      | f = 2400 MHz; I <sub>CC(tot)</sub> = 6 mA | -   | 1.2  | -   | dB   |



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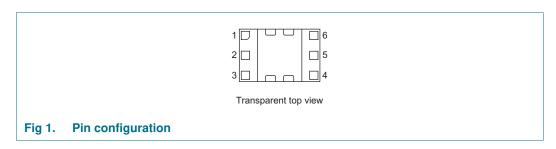
Table 1. Quick reference data ...continued

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 3.0 V;  $I_{CC(tot)}$  = 3.0 mA;  $V_{ENABLE}$   $\geq$  1.2 V unless otherwise specified. All measurements done on characterization board without matching, de-embedded up to the pins.

| Symbol              | Parameter                             | Conditions                                | Min | Тур  | Max | Unit |
|---------------------|---------------------------------------|---|-----|------|-----|------|
| P <sub>L(1dB)</sub> | output power at 1 dB gain compression | f = 450 MHz                               | -   | -5.0 | -   | dBm  |
|                     |                                       | f = 900 MHz                               | -   | -5.5 | -   | dBm  |
|                     |                                       | f = 2400 MHz; I <sub>CC(tot)</sub> = 6 mA | -   | 0    | -   | dBm  |
| IP3 <sub>O</sub>    | output third-order intercept point    | f = 450 MHz                               | -   | 5.5  | -   | dBm  |
|                     |                                       | f = 900 MHz                               | -   | 6.0  | -   | dBm  |
|                     |                                       | f = 2400 MHz; I <sub>CC(tot)</sub> = 6 mA | -   | 11.5 | -   | dBm  |

## 2. Pinning information

#### 2.1 Pinning



#### 2.2 Pin description

Table 2. Pin description

| Symbol          | Pin | Description                  |
|-----------------|-----|------------------------------|
| V <sub>CC</sub> | 1   | supply voltage               |
| n.c.            | 2   | not connected                |
| RF_IN           | 3   | RF in                        |
| RF_OUT          | 4   | RF out                       |
| ENABLE          | 5   | enable                       |
| CUR_ADJ         | 6   | current adjust               |
| GND             | GND | ground pad; RF and DC ground |

## 3. Ordering information

Table 3. Ordering information

| To the last to the |         |  |         |  |  |  |  |  |
|--|---------|--|---------|--|--|--|--|--|
| Type number  | Package |  |         |  |  |  |  |  |
|  | Name    | Description  | Version |  |  |  |  |  |
| BGU6102  | HXSON6  | plastic thermal enhanced super thin small outline package; no leads; 6 terminals; body 2 x 1.3 x 0.35 mm | SOT1209 |  |  |  |  |  |
| OM7809   | -       | 50 $\Omega$ LNA evaluation board   | -       |  |  |  |  |  |
| OM7810   | -       | high-ohmic LNA evaluation board  | -       |  |  |  |  |  |

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## 4. Marking

Table 4. Marking

| 3           |                              |                          |  |
|-------------|------------------------------|--------------------------|--|
| Type number | Marking                      | Description              |  |
| BGU6102     | 1B* $* = p : made in Hong R$ |                          |  |
|             |                              | * = t : made in Malaysia |  |
|             |                              | * = W : made in China    |  |

## 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                       | Conditions   | Min             | Max            | Unit |
|------------------|---------------------------------|--|-----------------|----------------|------|
| $V_{CC}$         | supply voltage                  | RF input, AC coupled   | -               | 5.5            | V    |
| $V_{ENABLE}$     | voltage on pin ENABLE           |  | <u>[1]</u> –0.5 | $V_{CC} + 1.8$ | V    |
| $V_{RF\_IN}$     | voltage on pin IN               | DC   | <b>2</b> –0.5   | +0.9           | V    |
| $V_{RF\_OUT}$    | voltage on pin RF_OUT           | DC   | -0.5            | $V_{CC} + 1.8$ | V    |
| $I_{CC(tot)}$    | total supply current            | $V_{CC} = 5.0 \text{ V}$   | -               | 40             | mA   |
| $T_{stg}$        | storage temperature             |  | -55             | +150           | °C   |
| Tj               | junction temperature            |  | -               | 150            | °C   |
| V <sub>ESD</sub> | electrostatic discharge voltage | Human Body Model (HBM); according to JEDEC standard 22-A114E     | -               | 3000           | V    |
|                  |                                 | Charged Device Model (CDM); according to JEDEC standard 22-C101B | -               | 500            | V    |

<sup>[1]</sup> Due to internal ESD diode protection, the applied voltage should not exceed the specified maximum in order to avoid excess current.

#### 6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter  | Conditions | Тур | Unit |
|----------------|--|------------|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |            | 110 | K/W  |

#### 7. Static characteristics

Table 7. Static characteristics

| Symbol               | Parameter            | Conditions                  |            | Min | Тур | Max  | Unit |
|----------------------|----------------------|-----------------------------|------------|-----|-----|------|------|
| $V_{CC}$             | supply voltage       | RF input, AC coupled        |            | 1.5 | -   | 5.0  | V    |
| I <sub>CC(tot)</sub> | total supply current | $V_{CC} = 3.0 \text{ V}$    | [1][2]     | 2.1 | -   | 21   | mA   |
|                      |                      | V <sub>ENABLE</sub> ≤ 0.4 V | <u>[1]</u> | -   | -   | 0.01 | mA   |
| T <sub>amb</sub>     | ambient temperature  |                             |            | -40 | +25 | +85  | °C   |

<sup>[1]</sup>  $I_{CC(tot)} = I_{CC} + I_{RF\_OUT} + I_{R\_BIAS}$ .

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<sup>[2]</sup> The RF input is directly coupled to the base of the RF transistor.

<sup>[2]</sup> Configurable with external resistor.

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## 8. Dynamic characteristics

Table 8. Dynamic characteristics

| Symbol           | Parameter                             | Conditions                    | Min | Тур  | Max | Unit |
|------------------|---------------------------------------|-------------------------------|-----|------|-----|------|
| 100 MHz          | frequency                             |                               |     |      |     |      |
| $ s_{21} ^2$     | insertion power gain                  | f = 100 MHz                   |     |      |     |      |
|                  |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 16.0 | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 19.5 | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 24.5 | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 28.0 | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 31.5 | -   | dB   |
| MSG              | maximum stable gain                   | f = 100 MHz                   |     |      |     |      |
|                  |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 29.0 | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 31.0 | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 33.5 | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 35.5 | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 37.5 | -   | dB   |
| $NF_{min}$       | minimum noise figure                  | f = 100 MHz                   |     |      |     |      |
|                  |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 8.0  | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 0.7  | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 8.0  | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 8.0  | -   | dB   |
|                  |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 1.0  | -   | dB   |
| $P_{L(1dB)} \\$  | output power at 1 dB gain compression | f = 100 MHz                   |     |      |     |      |
|                  |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | -6.0 | -   | dBm  |
|                  |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | -4.5 | -   | dBm  |
|                  |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 0.5  | -   | dBm  |
|                  |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 4.0  | -   | dBm  |
|                  |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 9.5  | -   | dBm  |
| IP3 <sub>O</sub> | output third-order intercept point    | f = 100 MHz                   |     |      |     |      |
|                  |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 3.0  | -   | dBm  |
|                  |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 5.5  | -   | dBm  |
|                  |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 10.5 | -   | dBm  |
|                  |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 14.5 | -   | dBm  |
|                  |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 19.5 | -   | dBm  |

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

| Symbol              | Parameter                             | Conditions                    | Min | Тур  | Max | Unit |
|---------------------|---------------------------------------|-------------------------------|-----|------|-----|------|
| 150 MHz             | frequency                             |                               |     |      |     |      |
| $ s_{21} ^2$        | insertion power gain                  | f = 150 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 16.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 19.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 24.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 27.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 31.0 | -   | dB   |
| MSG                 | maximum stable gain                   | f = 150 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 27.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 29.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 32.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 34.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 36.0 | -   | dB   |
| $NF_{min}$          | minimum noise figure                  | f = 150 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 8.0  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 0.7  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 8.0  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 8.0  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 1.0  | -   | dB   |
| P <sub>L(1dB)</sub> | output power at 1 dB gain compression | f = 150 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | -6.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | -4.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 0.0  | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 3.5  | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 9.0  | -   | dBm  |
| IP3 <sub>O</sub>    | output third-order intercept point    | f = 150 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 3.0  | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 5.5  | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 10.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 14.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 19.5 | -   | dBm  |

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

| Symbol              | Parameter                             | Conditions                    | Min | Тур  | Max | Unit |
|---------------------|---------------------------------------|-------------------------------|-----|------|-----|------|
| 450 MHz             | frequency                             |                               |     |      |     |      |
| $ s_{21} ^2$        | insertion power gain                  | f = 450 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 15.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 18.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 23.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 26.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 29.0 | -   | dB   |
| MSG                 | maximum stable gain                   | f = 450 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 22.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 24.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 27.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 29.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 31.0 | -   | dB   |
| $NF_{min}$          | minimum noise figure                  | f = 450 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 8.0  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 0.7  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 8.0  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 8.0  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 1.0  | -   | dB   |
| P <sub>L(1dB)</sub> | output power at 1 dB gain compression | f = 450 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | -7.0 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | -5.0 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | -0.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 3.0  | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 9.0  | -   | dBm  |
| IP3 <sub>O</sub>    | output third-order intercept point    | f = 450 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 3.0  | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 5.5  | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 10.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 14.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 19.5 | -   | dBm  |

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

| Symbol              | Parameter                             | Conditions                    | Min | Тур  | Max | Unit |
|---------------------|---------------------------------------|-------------------------------|-----|------|-----|------|
| 900 MHz             | frequency                             |                               |     |      |     |      |
| $ s_{21} ^2$        | insertion power gain                  | f = 900 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 14.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 16.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 20.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 23.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 25.0 | -   | dB   |
| MSG                 | maximum stable gain                   | f = 900 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 19.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 21.5 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 24.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 26.0 | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 28.0 | -   | dB   |
| $NF_{min}$          | minimum noise figure                  | f = 900 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 8.0  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 8.0  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 0.7  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 8.0  | -   | dB   |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 1.0  | -   | dB   |
| P <sub>L(1dB)</sub> | output power at 1 dB gain compression | f = 900 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | -7.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | -5.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | -0.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 3.5  | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 10.0 | -   | dBm  |
| IP3 <sub>O</sub>    | output third-order intercept point    | f = 900 MHz                   |     |      |     |      |
|                     |                                       | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 3.5  | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 6.0  | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 11.5 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 15.0 | -   | dBm  |
|                     |                                       | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 21.0 | -   | dBm  |

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 Table 8.
 Dynamic characteristics ...continued

| Symbol  | Parameter                           | Conditions                    | Min | Тур  | Max | Unit |
|---|-------------------------------------|-------------------------------|-----|------|-----|------|
| 1500 MH   | z frequency                         |                               |     |      |     |      |
| $ s_{21} ^2$  | insertion power gain                | f = 1500 MHz                  |     |      |     |      |
|   |                                     | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 11.5 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 14.0 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 17.5 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 19.5 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 21.0 | -   | dB   |
| MSG   | maximum stable gain                 | f = 1500 MHz                  |     |      |     |      |
|   |                                     | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 18.0 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 19.5 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 22.0 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 24.0 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 25.5 | -   | dB   |
| $NF_{min}$  | <sub>min</sub> minimum noise figure | f = 1500 MHz                  |     |      |     |      |
|   |                                     | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 1.0  | -   | dB   |
|   |                                     | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 1.0  | -   | dB   |
|   |                                     | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 0.9  | -   | dB   |
|   |                                     | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 0.9  | -   | dB   |
|   |                                     | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 1.0  | -   | dB   |
| P <sub>L(1dB)</sub> output power at 1 dB gain compression |                                     | f = 1500 MHz                  |     |      |     |      |
|   |                                     | $I_{CC(tot)} = 2 \text{ mA}$  | -   | -7.5 | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 3 \text{ mA}$  | -   | -5.5 | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 0.0  | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 4.0  | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 10.5 | -   | dBm  |
| IP3 <sub>O</sub>  | output third-order intercept point  | f = 1500 MHz                  |     |      |     |      |
|   |                                     | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 3.5  | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 6.5  | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 12.5 | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 16.5 | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 21.5 | -   | dBm  |

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

| Symbol  | Parameter                          | Conditions                    | Min | Тур  | Max | Unit |
|---|------------------------------------|-------------------------------|-----|------|-----|------|
| 1900 MH   | z frequency                        |                               |     |      |     |      |
| $ s_{21} ^2$  | insertion power gain               | f = 1900 MHz                  |     |      |     |      |
|   |                                    | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 10.5 | -   | dB   |
|   |                                    | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 12.5 | -   | dB   |
|   |                                    | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 16.0 | -   | dB   |
|   |                                    | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 17.5 | -   | dB   |
|   |                                    | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 19.0 | -   | dB   |
| MSG   | maximum stable gain                | f = 1900 MHz                  |     |      |     |      |
|   |                                    | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 17.0 | -   | dB   |
|   |                                    | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 18.5 | -   | dB   |
|   |                                    | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 21.5 | -   | dB   |
|   |                                    | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 23.0 | -   | dB   |
|   |                                    | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 24.5 | -   | dB   |
| $NF_{min}$  | minimum noise figure               | f = 1900 MHz                  |     |      |     |      |
|   |                                    | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 1.1  | -   | dB   |
|   |                                    | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 1.1  | -   | dB   |
|   |                                    | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 1.0  | -   | dB   |
|   |                                    | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 1.0  | -   | dB   |
|   |                                    | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 1.1  | -   | dB   |
| P <sub>L(1dB)</sub> output power at 1 dB gain compression |                                    | f = 1900 MHz                  |     |      |     |      |
|   |                                    | $I_{CC(tot)} = 2 \text{ mA}$  | -   | -7.5 |     | dBm  |
|   |                                    | $I_{CC(tot)} = 3 \text{ mA}$  | -   | -5.5 | -   | dBm  |
|   |                                    | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 0.0  | -   | dBm  |
|   |                                    | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 4.5  | -   | dBm  |
|   |                                    | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 10.5 | -   | dBm  |
| IP3 <sub>O</sub>  | output third-order intercept point | f = 1900 MHz                  |     |      |     |      |
|   |                                    | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 3.0  | -   | dBm  |
|   |                                    | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 6.5  | -   | dBm  |
|   |                                    | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 12.0 | -   | dBm  |
|   |                                    | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 16.0 | -   | dBm  |
|   |                                    | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 21   | -   | dBm  |

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

| Symbol  | Parameter                           | Conditions                    | Min | Тур  | Max | Unit |
|---|-------------------------------------|-------------------------------|-----|------|-----|------|
| 2400 MH   | z frequency                         |                               |     |      |     |      |
| $ s_{21} ^2$  | insertion power gain                | f = 2400 MHz                  |     |      |     |      |
|   |                                     | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 8.5  | -   | dB   |
|   |                                     | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 11.0 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 14.0 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 15.5 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 17.0 | -   | dB   |
| MSG   | maximum stable gain                 | f = 2400 MHz                  |     |      |     |      |
|   |                                     | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 16.5 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 18.0 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 20.5 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 22.0 | -   | dB   |
|   |                                     | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 23.0 | -   | dB   |
| NF <sub>min</sub>   | <sub>nin</sub> minimum noise figure | f = 2400 MHz                  |     |      |     |      |
|   |                                     | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 1.5  | -   | dB   |
|   |                                     | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 1.3  | -   | dB   |
|   |                                     | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 1.2  | -   | dB   |
|   |                                     | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 1.2  | -   | dB   |
|   |                                     | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 1.3  | -   | dB   |
| P <sub>L(1dB)</sub> output power at 1 dB gain compression |                                     | f = 2400 MHz                  |     |      |     |      |
|   |                                     | $I_{CC(tot)} = 2 \text{ mA}$  | -   | -7.5 | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 3 \text{ mA}$  | -   | -5.0 | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 0.0  | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 4.5  | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 10.5 | -   | dBm  |
| IP3 <sub>O</sub>  | output third-order intercept point  | f = 2400 MHz                  |     |      |     |      |
|   |                                     | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 2.5  | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 6.0  | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 11.5 | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 16.0 | -   | dBm  |
|   |                                     | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 20.0 | -   | dBm  |

#### Wideband silicon low-noise amplifier MMIC

 Table 8.
 Dynamic characteristics ...continued

| Symbol            | Parameter   | Conditions                    | Min | Тур  | Max | Unit |
|-------------------|---|-------------------------------|-----|------|-----|------|
| 3500 MH           | z frequency                                       |                               |     |      |     |      |
| $ s_{21} ^2$      | insertion power gain                              | f = 3500 MHz                  |     |      |     |      |
|                   |   | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 5.5  | -   | dB   |
|                   |   | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 7.5  | -   | dB   |
|                   |   | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 10.5 | -   | dB   |
|                   |   | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 12.0 | -   | dB   |
|                   |   | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 13.5 | -   | dB   |
| MSG               | maximum stable gain                               | f = 3500 MHz                  |     |      |     |      |
|                   | $I_{CC(tot)} = 2 \text{ mA} \qquad - \qquad 16.0$ | 16.0                          | -   | dB   |     |      |
|                   |   | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 17.5 | -   | dB   |
|                   |   | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 19.0 | -   | dB   |
|                   |   | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 18.5 | -   | dB   |
|                   |   | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 18.5 | -   | dB   |
| NF <sub>min</sub> | minimum noise figure                              | f = 3500 MHz                  |     |      |     |      |
|                   |   | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 2.3  | -   | dB   |
|                   |   | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 2.2  | -   | dB   |
|                   |   | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 1.9  | -   | dB   |
|                   |   | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 1.8  | -   | dB   |
|                   |   | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 1.9  | -   | dB   |
| $P_{L(1dB)} \\$   | output power at 1 dB gain compression             | f = 3500 MHz                  |     |      |     |      |
|                   |   | $I_{CC(tot)} = 2 \text{ mA}$  | -   | -7.5 | -   | dBm  |
|                   |   | $I_{CC(tot)} = 3 \text{ mA}$  | -   | -5.5 | -   | dBm  |
|                   |   | $I_{CC(tot)} = 6 \text{ mA}$  | -   | -0.5 | -   | dBm  |
|                   |   | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 4.5  | -   | dBm  |
|                   |   | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 9.5  | -   | dBm  |
| IP3 <sub>O</sub>  | output third-order intercept point                | f = 3500 MHz                  |     |      |     |      |
|                   |   | $I_{CC(tot)} = 2 \text{ mA}$  | -   | 2.5  | -   | dBm  |
|                   |   | $I_{CC(tot)} = 3 \text{ mA}$  | -   | 6.0  | -   | dBm  |
|                   |   | $I_{CC(tot)} = 6 \text{ mA}$  | -   | 11.5 | -   | dBm  |
|                   |   | $I_{CC(tot)} = 10 \text{ mA}$ | -   | 16.5 | -   | dBm  |
|                   |   | $I_{CC(tot)} = 20 \text{ mA}$ | -   | 20.0 | -   | dBm  |

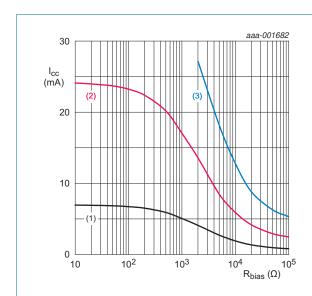
#### Wideband silicon low-noise amplifier MMIC

## 9. Enable control

Table 9. ENABLE (pin 5)

-40 °C  $\leq T_{amb} \leq +85$  °C.

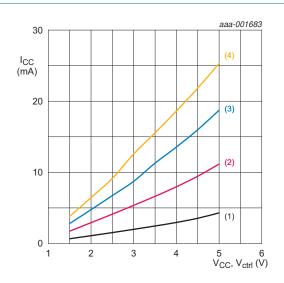
| V <sub>ENABLE</sub> (V) | State |
|-------------------------|-------|
| ≤ 0.4                   | OFF   |
| ≥ 1.2                   | ON    |



 $T_{amb}$  = 25 °C.

- (1)  $V_{CC} = 1.5 \text{ V}$
- (2)  $V_{CC} = 3 V$
- (3)  $V_{CC} = 5 V$

Fig 2. Supply current as a function of bias resistor; typical values

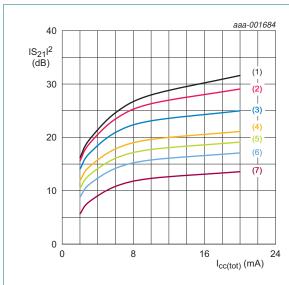


 $T_{amb} = 25 \, ^{\circ}C.$ 

- (1) R<sub>bias</sub> = OPEN
- (2)  $R_{bias} = 12 \text{ k}\Omega$
- (3)  $R_{bias} = 4.7 \text{ k}\Omega$
- (4)  $R_{bias} = 2.4 \text{ k}\Omega$

Fig 3. Supply current as a function of supply voltage and control voltage; typical values

#### Wideband silicon low-noise amplifier MMIC



 $T_{amb}$  = 25 °C;  $V_{CC}$  = 3 V;  $P_i$  = -30 dBm.

(1) f = 150 MHz

(2) f = 450 MHz

(3) f = 900 MHz

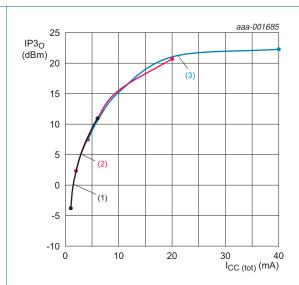
(4) f = 1500 MHz

(5) f = 1900 MHz

(6) f = 2400 MHz

(7) f = 3500 MHz

Fig 4. Insertion power gain  $(|s_{21}|^2)$  as a function of total supply current; typical values



 $T_{amb}$  = 25 °C;  $f_1$  = 900 MHz;  $f_2$  = 900.2 MHz;  $P_i$  = -30 dBm.

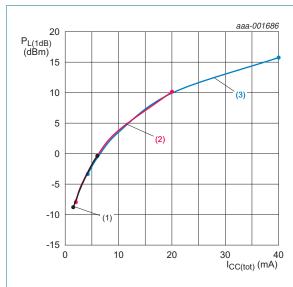
(1)  $V_{CC} = 1.5 \text{ V}$ 

(2)  $V_{CC} = 3 V$ 

(3)  $V_{CC} = 5 \text{ V}$ 

Fig 5. Output third-order intercept point as a function of total supply current; typical values

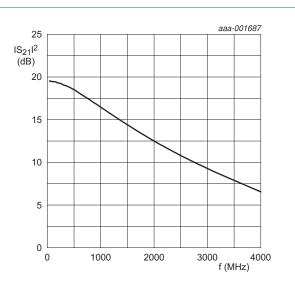
#### Wideband silicon low-noise amplifier MMIC



 $T_{amb}$  = 25 °C; f = 900 MHz.

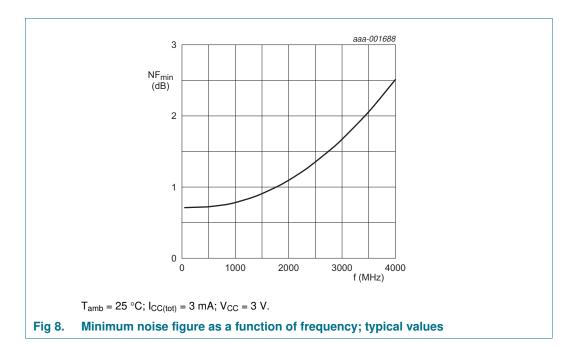
- (1)  $V_{CC} = 1.5 \text{ V}$
- (2)  $V_{CC} = 3 V$
- (3)  $V_{CC} = 5 V$

Fig 6. Output power at 1 dB gain compression as a function of total supply current; typical values



 $T_{amb}$  = 25 °C;  $I_{CC(tot)}$  = 3 mA;  $V_{CC}$  = 3 V;  $P_i$  = -30 dBm.

Fig 7. Insertion power gain  $(|s_{21}|^2)$  as a function of frequency; typical values



#### Wideband silicon low-noise amplifier MMIC

## 10. Application information

Other applications available. Please contact your local sales representative for more information. Application note(s) available on the NXP web site.

All measurements are done with the SAM connector as reference plane.

#### 10.1 High-ohmic FM radio characteristics

Table 10. AC characteristics[1]

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 3.0 V;  $I_{CC(tot)}$  = 3.1 mA; f = 100 MHz; measurements done on high-ohmic FM radio application board.

| Symbol              | Parameter                            | Conditions        | Min | Тур | Max | Unit |
|---------------------|--------------------------------------|-------------------|-----|-----|-----|------|
| $ s_{21} ^2$        | insertion power gain                 |                   | -   | 13  | -   | dB   |
| $RL_{in}$           | input return loss                    |                   | -   | 1   | -   | dB   |
| $RL_{out}$          | output return loss                   |                   | -   | 20  | -   | dB   |
| NF                  | noise figure                         | $Z_S = 50 \Omega$ | -   | 1.0 | -   | dB   |
| P <sub>i(1dB)</sub> | input power at 1 dB gain compression |                   | -   | -23 | -   | dBm  |
| IP3 <sub>I</sub>    | input third-order intercept point    |                   | -   | -15 | -   | dBm  |

<sup>[1]</sup> See application note AN11091 for details.

#### 10.2 50 ohm FM radio characteristics

Table 11. AC characteristics[1]

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 2.8 V;  $I_{CC(tot)}$  = 4.3 mA; f = 100 MHz; measurements done on 50  $\Omega$  application board.

| Symbol              | Parameter                            | Conditions        | Min | Тур | Max | Unit |
|---------------------|--------------------------------------|-------------------|-----|-----|-----|------|
| $ s_{21} ^2$        | insertion power gain                 |                   | -   | 15  | -   | dB   |
| RLin                | input return loss                    |                   | -   | 10  | -   | dB   |
| RLout               | output return loss                   |                   | -   | 14  | -   | dB   |
| NF                  | noise figure                         | $Z_S = 50 \Omega$ | -   | 1.3 | 1.8 | dB   |
| P <sub>i(1dB)</sub> | input power at 1 dB gain compression |                   | -   | -20 | -   | dBm  |
| IP3 <sub>I</sub>    | input third-order intercept point    |                   | -   | -12 | -   | dBm  |

<sup>[1]</sup> See application note AN11090 for details.

#### Wideband silicon low-noise amplifier MMIC

## 11. Package outline

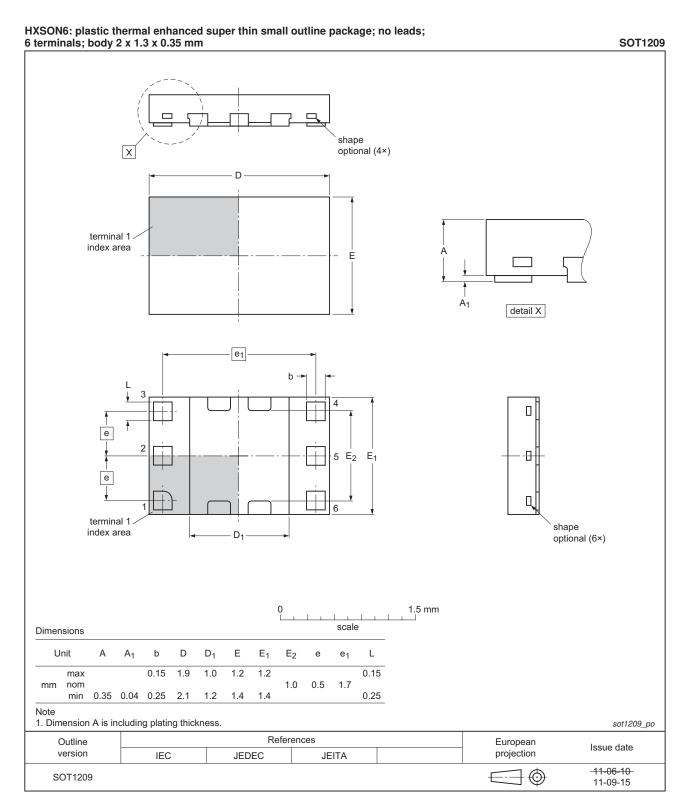


Fig 9. Package outline SOT1209

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#### Wideband silicon low-noise amplifier MMIC

## 12. Abbreviations

Table 12. Abbreviations

| Acronym | Description                             |
|---------|---|
| AMR     | Automated Meter Reading                 |
| CMMB    | China Mobile Multimedia Broadcasting    |
| ESD     | ElectroStatic Discharge                 |
| FM      | Frequency Modulation                    |
| ISM     | Industrial Scientific Medical           |
| LNA     | Low-Noise Amplifier                     |
| MMIC    | Monolithic Microwave Integrated Circuit |
| RKE     | Remote Keyless Entry                    |
| TPMS    | Tire-Pressure Monitoring System         |
| WLAN    | Wireless Local Area Network             |

# 13. Revision history

#### Table 13. Revision history

| Release date | Data sheet status                             | Change notice   | Supersedes  |
|--------------|---|---|---|
| 20120713     | Product data sheet                            | -   | BGU6102 v.2   |
| • Table 5 on | page 3: changed the layout ir                 | order to remove the v   |   |
| 20120203     | Product data sheet                            | -   | BGU6102 v.1   |
| 20110921     | Preliminary data sheet                        | -   | -   |
|              | 20120713  • Table 3 on and to reduce 20120203 | <ul> <li>20120713 Product data sheet</li> <li>Table 3 on page 2: swapped the description</li> <li>Table 5 on page 3: changed the layout in and to reduce the page count with one page 20120203</li> <li>Product data sheet</li> </ul> | 20120713 Product data sheet  • Table 3 on page 2: swapped the descriptions of OM7809 and Company of the second of |

#### Wideband silicon low-noise amplifier MMIC

## 14. Legal information

#### 14.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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#### Wideband silicon low-noise amplifier MMIC

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